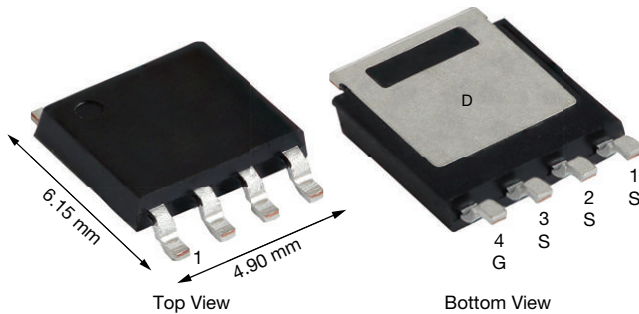
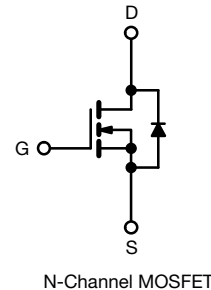


# Automotive N-Channel 80 V (D-S) 175 °C MOSFET

**PowerPAK® SO-8L**

**FEATURES**

- TrenchFET® Gen IV power MOSFET
- AEC-Q101 qualified
- 100 % R<sub>g</sub> and UIS tested
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)

 AUTOMOTIVE  
GRADE

**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**


N-Channel MOSFET

**PRODUCT SUMMARY**

V <sub>DS</sub> (V)	80
R <sub>DS(on)</sub> (Ω) at V <sub>GS</sub> = 10 V	0.0075
I <sub>D</sub> (A)	118
Configuration	Single
Package	PowerPAK SO-8L

**ABSOLUTE MAXIMUM RATINGS** (T<sub>C</sub> = 25 °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-source voltage	V <sub>DS</sub>	80	V
Gate-source voltage	V <sub>GS</sub>	± 20	
Continuous drain current	I <sub>D</sub>	T <sub>C</sub> = 25 °C	118
		T <sub>C</sub> = 125 °C	68
Continuous source current (diode conduction)	I <sub>S</sub>	210	A
Pulsed drain current	I <sub>DM</sub>	240	
Single pulse avalanche current	L = 0.1 mH	E <sub>AS</sub>	32
Single pulse avalanche energy			51
Maximum power dissipation	P <sub>D</sub>	T <sub>C</sub> = 25 °C	234
		T <sub>C</sub> = 125 °C	78
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C
Soldering recommendations (peak temperature) <sup>b</sup>		260	

**THERMAL RESISTANCE RATINGS**

PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-ambient	R <sub>thJA</sub>	42	°C/W
Junction-to-case (drain)	R <sub>thJC</sub>	0.64	

**Notes**

- When mounted on 1" square PCB (FR4 material)
- See solder profile ([www.vishay.com/doc?73257](http://www.vishay.com/doc?73257)). The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection



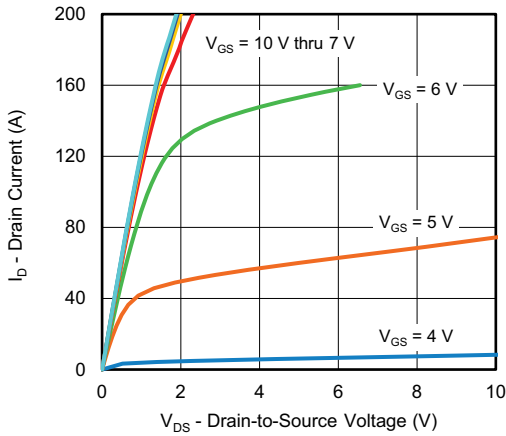
<b>SPECIFICATIONS</b> ( $T_C = 25\text{ }^\circ\text{C}$ , unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
<b>Static</b>						
Drain-source breakdown voltage	$V_{DS}$	$V_{GS} = 0, I_D = 250\text{ }\mu\text{A}$	80	-	-	V
Gate-source threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2.2	2.7	3.5	
Gate-source leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$	-	-	$\pm 100$	nA
Zero gate voltage drain current	$I_{DSS}$	$V_{GS} = 0\text{ V}$ $V_{DS} = 80\text{ V}$	-	-	1	$\mu\text{A}$
		$V_{GS} = 0\text{ V}$ $V_{DS} = 80\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	-	50	
		$V_{GS} = 0\text{ V}$ $V_{DS} = 80\text{ V}, T_J = 175\text{ }^\circ\text{C}$	-	-	250	
On-state drain current <sup>a</sup>	$I_{D(on)}$	$V_{GS} = 10\text{ V}$ $V_{DS} \geq 5\text{ V}$	30	-	-	A
Drain-source on-state resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$ $I_D = 15\text{ A}$	-	0.0060	0.0075	$\Omega$
		$V_{GS} = 10\text{ V}$ $I_D = 15\text{ A}, T_J = 125\text{ }^\circ\text{C}$	-	-	0.0124	
		$V_{GS} = 10\text{ V}$ $I_D = 15\text{ A}, T_J = 175\text{ }^\circ\text{C}$	-	-	0.0156	
Forward transconductance <sup>b</sup>	$g_{fs}$	$V_{DS} = 15\text{ V}, I_D = 10\text{ A}$	-	67	-	S
<b>Dynamic <sup>b</sup></b>						
Input capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}$ $V_{DS} = 25\text{ V}, f = 1\text{ MHz}$	-	2484	3478	$\mu\text{F}$
Output capacitance	$C_{oss}$		-	1029	1441	
Reverse transfer capacitance	$C_{rss}$		-	76	107	
Total gate charge <sup>c</sup>	$Q_g$	$V_{GS} = 10\text{ V}$ $V_{DS} = 40\text{ V}, I_D = 30\text{ A}$	-	46	69	nC
Gate-source charge <sup>c</sup>	$Q_{gs}$		-	12	-	
Gate-drain charge <sup>c</sup>	$Q_{gd}$		-	13	-	
Gate resistance	$R_g$	$f = 1\text{ MHz}$	0.6	1.2	1.8	$\Omega$
Turn-on delay time <sup>c</sup>	$t_{d(on)}$	$V_{DD} = 40\text{ V}, R_L = 1.33\text{ }\Omega,$ $I_D \cong 30\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$	-	12	18	ns
Rise time <sup>c</sup>	$t_r$		-	4	6	
Turn-off delay time <sup>c</sup>	$t_{d(off)}$		-	23	35	
Fall time <sup>c</sup>	$t_f$		-	5	8	
<b>Source-Drain Diode Ratings and Characteristics <sup>b</sup></b>						
Pulsed current <sup>a</sup>	$I_{SM}$		-	-	240	A
Forward voltage	$V_{SD}$	$I_F = 15\text{ A}, V_{GS} = 0\text{ V}$	-	-	1.1	V
Body diode reverse recovery time	$t_{rr}$	$I_F = 10\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$	-	37	74	ns
Body diode reverse recovery charge	$Q_{rr}$		-	38	76	nC
Reverse recovery fall time	$t_a$		-	21	-	ns
Reverse recovery rise time	$t_b$		-	15	-	
Body diode peak reverse recovery current	$I_{RM(REC)}$			-	-2.0	-

**Notes**

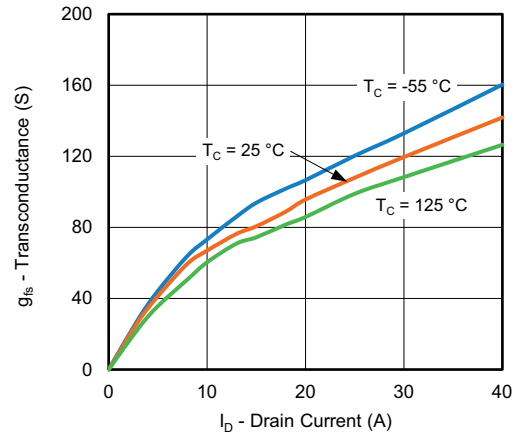
- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

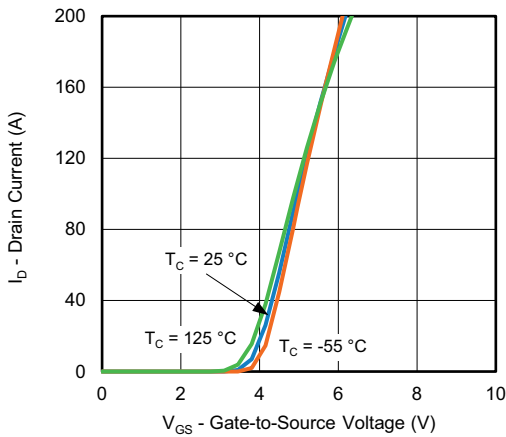
**TYPICAL CHARACTERISTICS** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)



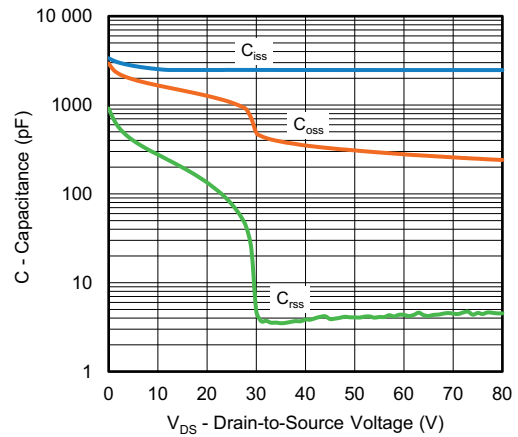
**Output Characteristics**



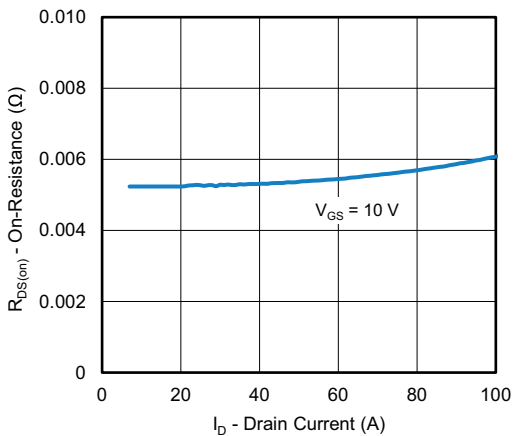
**Transconductance**



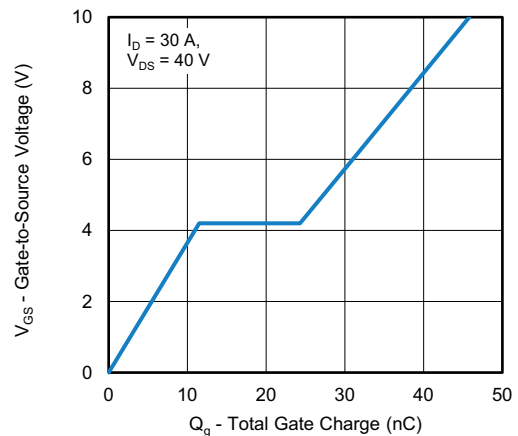
**Transfer Characteristics**



**Capacitance**



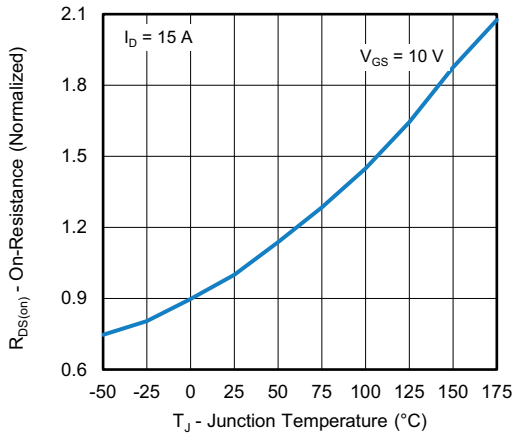
**On-Resistance vs. Drain Current**



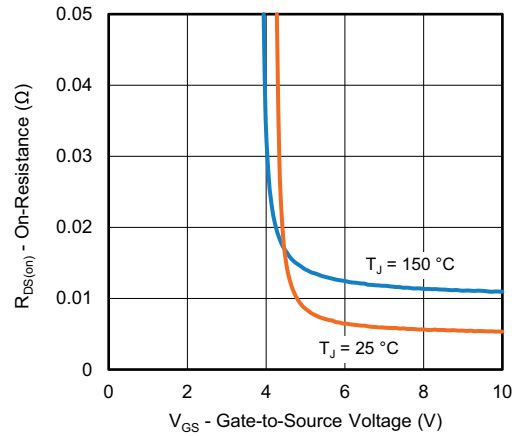
**Gate Charge**



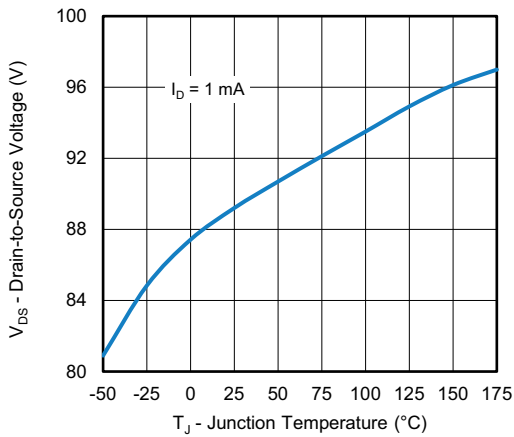
TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)



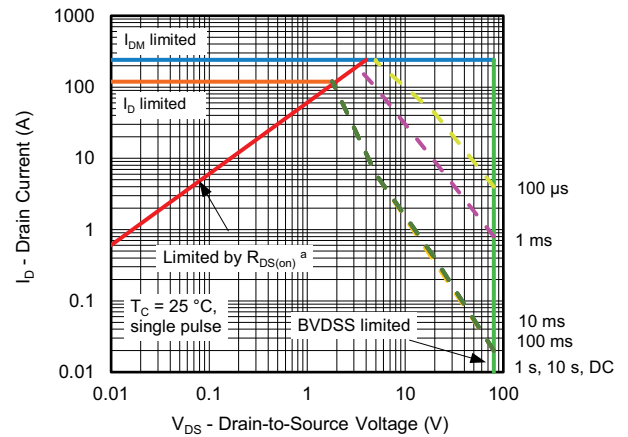
On-Resistance vs. Junction Temperature



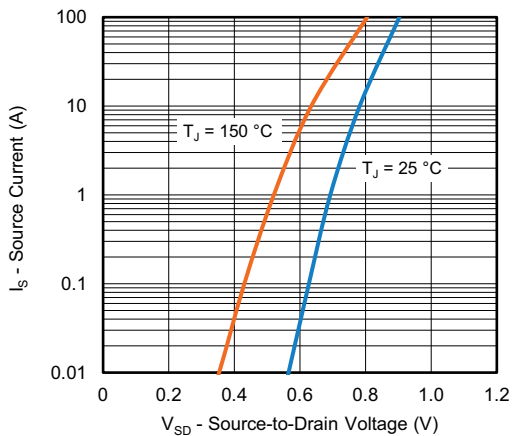
On-Resistance vs. Gate to Source Voltage



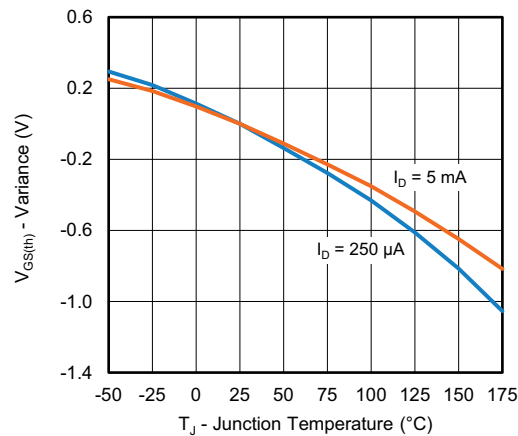
Drain Source Breakdown vs. Junction Temperature



Safe Operating Area



Source Drain Diode Forward Voltage



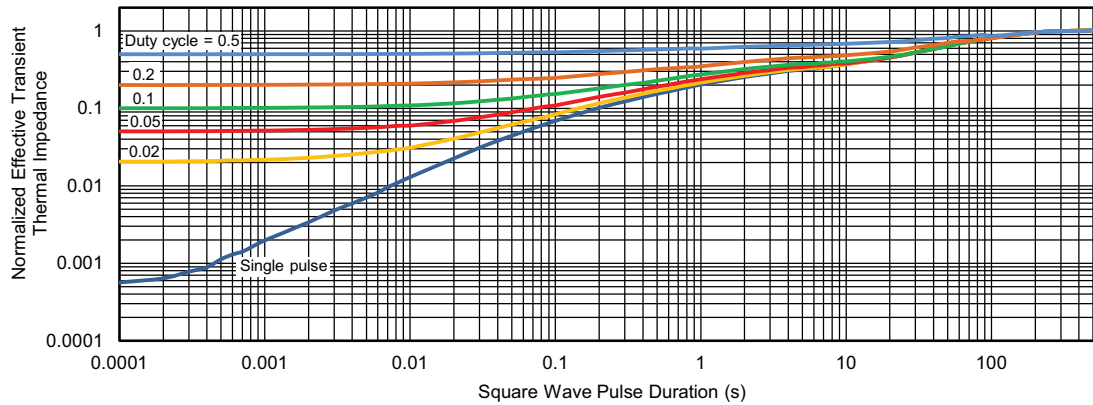
Threshold Voltage

Note

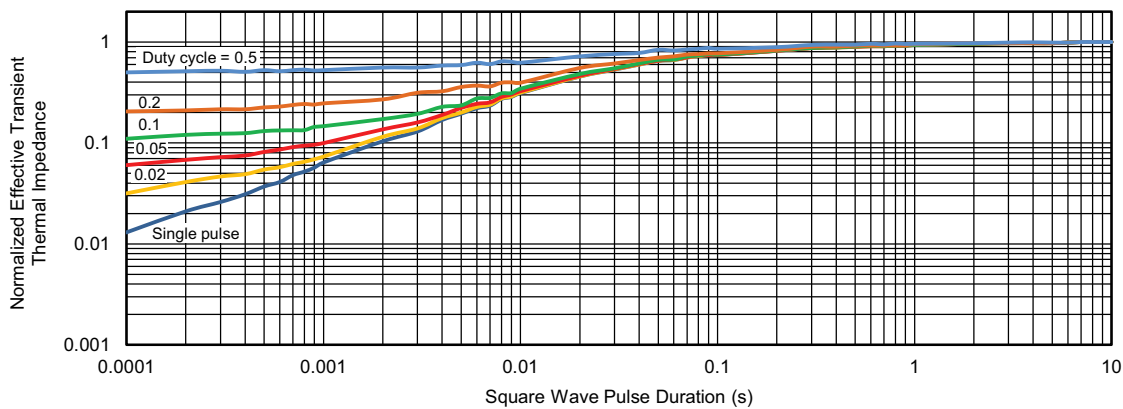
a. V<sub>GS</sub> > minimum V<sub>GS</sub> at which R<sub>DS(on)</sub> is specified



TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

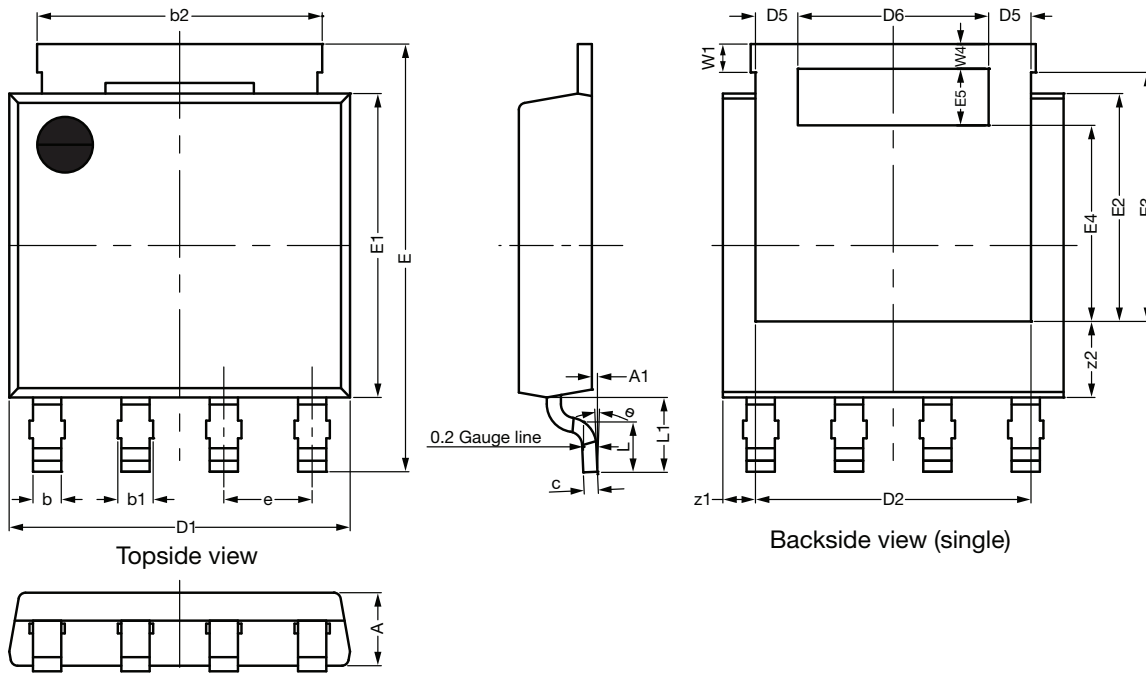
Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)
 are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

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### PowerPAK® SO-8L (PPKS08LWLA) Case Outline 3



DIM.	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	1.00	1.05	1.10	0.039	0.041	0.043
A1	0.00	---	0.127	0.000	---	0.005
b	0.33	0.41	0.49	0.013	0.016	0.019
b1	0.43	0.51	0.59	0.017	0.020	0.023
b2	4.00	4.10	4.20	0.157	0.161	0.165
c	0.15	0.20	0.25	0.006	0.008	0.010
D1	4.80	4.90	5.00	0.189	0.193	0.197
D2	3.86	3.96	4.06	0.152	0.156	0.160
D5	0.51	0.61	0.71	0.020	0.024	0.028
D6	2.64	2.74	2.84	0.104	0.108	0.112
e	1.27 BSC			0.050 BSC		
E	6.05	6.15	6.25	0.238	0.242	0.246
E1	4.27	4.37	4.47	0.168	0.172	0.176
E2	3.18	3.28	3.38	0.125	0.129	0.133
E3	3.48	3.58	3.68	0.137	0.141	0.145
E4	2.72	2.82	2.92	0.107	0.111	0.115
E5	0.71	0.81	0.91	0.028	0.032	0.036
L	0.62	0.72	0.82	0.024	0.028	0.032
L1	0.92	1.07	1.22	0.036	0.042	0.048
W1	0.31	0.41	0.51	0.012	0.016	0.020
W4	0.31	0.36	0.41	0.012	0.014	0.016
z1	0.37	0.47	0.57	0.015	0.019	0.022
z2	0.99	1.09	1.19	0.039	0.043	0.047
θ	0°	---	5°	0°	---	5°

ECN: C22-1223-Rev. C, 19-Dec-2022  
 DWG: 6067

**Note**

- Millimeter will govern





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